

# Low Capacitance TVS/ESD Protection Diode

#### **DESCRIPTION**

SLESD0301M is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for data, control or power lines. With Maximum capacitance of 15pF, SLESD0301M is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 ( ±15 kV air, ±8kV contact discharge ), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

SLESD0301M uses ultra-small DFN1006 package . Each SLESD0301M device can protect one data line . It offers system designers flexibility to protect single data line where space is a premium concern.

#### **FEATURES**

IEC 61000-4-4 (EFT) 40A (5/50 ns) Cable Discharge Event (CDE)

- ♦Package optimized for high-speed lines
- ♦Ultra-small package (1.0mm×0.6mm×0.4mm)
- ♦Protects one data, control or power line
- ♦Low capacitance: 15pF (Maximum)
- ♦Low leakage current
- ♦Low clamping voltage
- ♦Each I/O pin can withstand over 1000 ESD strikes for ±8kV contact discharge

# **MACHANICAL DATA**

- ♦DFN1006 package
- ♦Flammability Rating: UL 94V-0
- ♦ Packaging: Tape and Reel
- ♦ High temperature soldering guaranted:260 °C/10s
- ♦Reel size: 7 inch
- ♦MSL 1

### **ORDERING INFORMATION**

→ Device: SLESD0301M→ Package: DFN1006

♦ Marking: 3B

♦ Material: Halogen free♦ Packing: Tape & Reel

♦ Quantity per reel: 10,000pcs

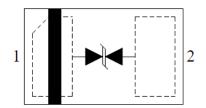
# **APPLICATIONS**

- ♦Portable Electronics
- ♦ Desktops, Servers and Notebooks
- ♦ Cellular Phones
- ♦MP3 Ports
- ♦ Digital Ports
- ♦Subscriber Identity Module (SIM) card

# **CIRCUIT DIAGRAM**



#### **PIN CONFIGURATION**





ABSOLUTE MAXIMUM RATING							
Symbol	Parameter	Value	Units				
V <sub>ESD</sub>	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±25 ±20	kV				
P <sub>PP</sub>	Peak Pulse Power (8/20µs)	84	W				
T <sub>OPT</sub>	Operating Temperature	-55/+125	°C				
T <sub>STG</sub>	Storage Temperature	-55/+150	°C				

ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
$V_{RWM}$	Reverse Working Voltage				3.3	V		
$V_{BR}$	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA	3.6			V		
I <sub>R</sub>	Reverse Leakage Current	$V_{RWM} = 3.3V$			1.0	μΑ		
V <sub>C</sub>	Clamping Voltage	$I_{PP} = 1A, t_p = 8/20 \mu s$			8.0	V		
Vc	Clamping Voltage	$I_{PPmax} = 7A$ , $t_p = 8/20 \mu s$			12.0	V		
CJ	Junction Capacitance	V <sub>R</sub> = 0V, f = 1MHz			15	pF		



